**What is claimed is:**

1. A method of manufacturing a semiconductor package including a substrate having a first surface, a second surface opposite said first surface, and interconnect patterns disposed therein, a semiconductor device mounted on said first surface of the substrate, a layer of sealing resin sealing said semiconductor device, a plurality of external connection electrodes formed on said second surface of the substrate, an electromagnetic wave shield film for blocking electromagnetic waves, said electromagnetic wave shield film being formed on an upper surface of said layer of sealing resin and side surfaces of said layer of sealing resin and said substrate, and a ground interconnect formed on said substrate and electrically connected to said electromagnetic wave shield film, said method comprising:

a package substrate preparing step of preparing a package substrate where semiconductor devices are placed in respective areas demarcated by a plurality of grid-like projected dicing lines and sealed by a layer of sealing resin, and a plurality of external connection electrodes are formed on the second surface opposite to the first surface sealed by said layer of sealing resin;

a protective film covering step of coating the second surface with the external connection electrodes formed thereon,

in its entirety with a liquid resin thereby to form a protective film thereon;

a dividing step of cutting said package substrate along the projected dicing lines with a cutting blade, so that the package substrate is divided into individual semiconductor packages, wherein the dividing step is performed after performing the protective film covering step;

an electromagnetic wave shield film forming step of applying a metal film to an upper surface of the layer of sealing resin on each of the semiconductor packages and side surfaces of each of the semiconductor packages, thereby forming an electromagnetic wave shield film for blocking electromagnetic waves, wherein the electromagnetic wave shield film forming step is performed after performing the protective film covering step; and

a protective film removing step of removing the protective film formed on the second surface, with the external connection electrodes formed thereon, of each of the semiconductor packages.

2. The method according to claim 1, further comprising:

a partial protective film removing step of, after performing the protective film covering step and before performing the dividing step, partly removing the protective

film on the projected dicing lines of the package substrate along the projected dicing lines.

3. The method according to claim 2, wherein said partial protective film removing step results in the removal of strips of the protective film, wherein said strips are wider than a thickness of the cutting blade used during said dividing step.

4. The method according claim 2, wherein said partial protective film removing step results in the removal of strips of the protective film, wherein said strips extend from an outer surface of the protective film to the second surface of the substrate.

5. The method according claim 2, wherein said partial protective film removing step results in the removal of strips of the protective film, wherein said strips do not extend into the substrate.

6. The method according to claim 1, wherein said electromagnetic wave shield film forming step is performed while the protective film is in direct contact with a dicing tape.

7. The method according to claim 1, wherein the ground

interconnect comprises a pair of ground interconnects that terminate short of the side surfaces of the semiconductor package, and further wherein the electromagnetic wave shield film also includes portions formed on the second surface of the substrate that are configured and arranged to be electrically connected to the pair of ground interconnects that terminate short of the side surfaces of the semiconductor package.

8. The method according to claim 1, further comprising:

a semiconductor packages supporting step of pasting a protective film side of the semiconductor packages to a dicing film, the outer periphery of the dicing film being applied to a frame to thereby support a plurality of semiconductor packages by the frame through the dicing tape, after performing said dividing step,

wherein said electromagnetic wave shield film forming step is performed after performing said semiconductor packages supporting step.

9. The method according to claim 3, wherein the electromagnetic wave shield film is formed not only on the upper surface of said layer of sealing resin and side surfaces of said layer of sealing resin and said substrate but is also

formed on partly on the second surface of said substrate in said electromagnetic wave shield film forming step.